

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-60V	4.2Ω@-10V	-130mA
	4.5Ω@-4.5V	



合肥矽普半导体

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Feature

- High power and current handling capability
- Surface mount package
- ESD Protected 2KV

Application

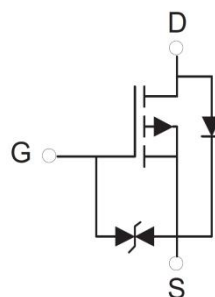
- Battery Switch
- DC/DC Converter

Package

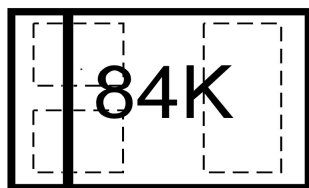


DFN1006-3L

Circuit diagram



Marking



B84K

:Device Code

Order Information

Device	Package	Unit/Tape
BSS84KNC	DFN1006-3L	10000

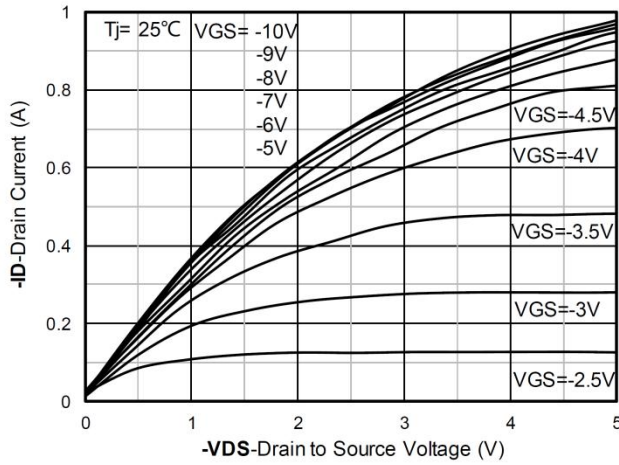
Absolute maximum ratings (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	-130	mA
Pulse Drain Current Tested	I_{DM}	-520	mA
Power Dissipation	P_D	150	mW
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	833	°C/W
Storage Temperature Range	T_{STG}	-55 to 150	°C
Operating Junction Temperature Range	T_J	-55 to 150	°C

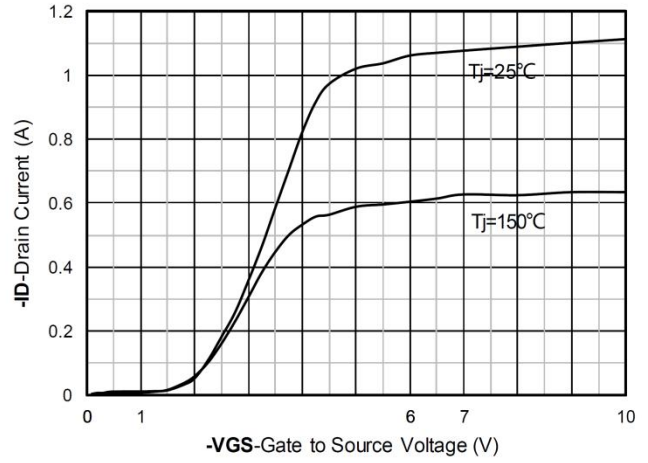
Electrical characteristics (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	VGS=0V , ID=-250μA	-60	-	-	V
Drain-Source Leakage Current	I _{DSS}	VDS=-48V , VGS=0V	-	-	-1	uA
Gate-Source Leakage Current	I _{GSS}	VGS=±20V , VDS=0V	-	-	±10	uA
Gate Threshold Voltage	VGS(th)	VDS=VGS , ID=-250μA	-0.8	-1.5	-2.5	V
Static Drain-Source On-Resistance	R _{DS(ON)}	VGS =-10V, ID =-150mA	-	4.2	6	Ω
		VGS =-4.5V, ID =-150mA	-	4.5	7	
Dynamic characteristics						
Input Capacitance	C _{iss}	VDS=-5V , VGS=0V , f=1MHz	-	30	-	pF
Output Capacitance	C _{oss}		-	10	-	
Reverse Transfer Capacitance	C _{rss}		-	5	-	
Total Gate Charge	Q _g	VDS=-30V , VGS=-10V , ID=-0.15A	-	1.8	-	nC
Gate-Source Charge	Q _{gs}		-	0.5	-	
Gate-Drain Charge	Q _{gd}		-	0.18	-	
Switching Characteristics						
Turn-On Delay Time	t _{d(on)}	VDD=-15V VGS=-10V , RG=50Ω, ID=-0.15A	-	8.6	-	nS
Turn-On Rise Time	t _r		-	20	-	
Turn-Off Delay Time	t _{d(off)}		-	14	-	
Turn-Off Fall Time	t _f		-	77	-	
Source-Drain Diode characteristics						
Diode Forward Voltage	V _{SD}	VGS=0V , IS=-1A , TJ=25℃	-	-	-1.2	V

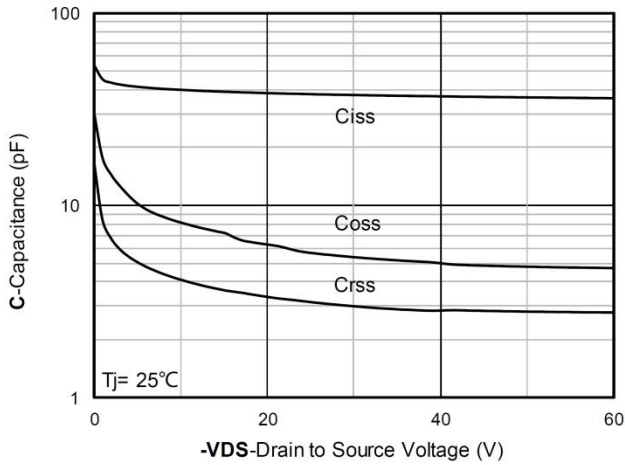
Typical Characteristics



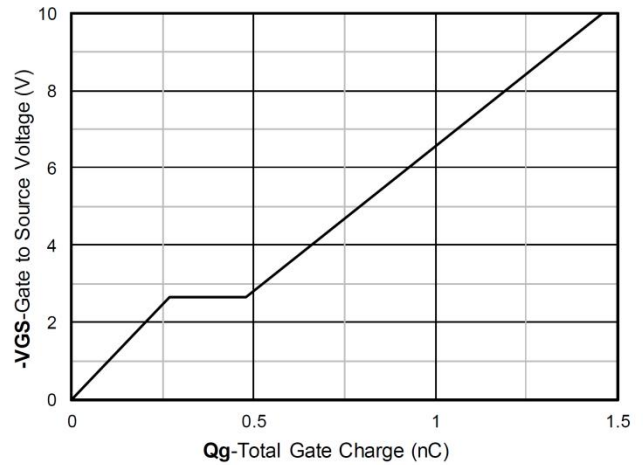
Output Characteristics



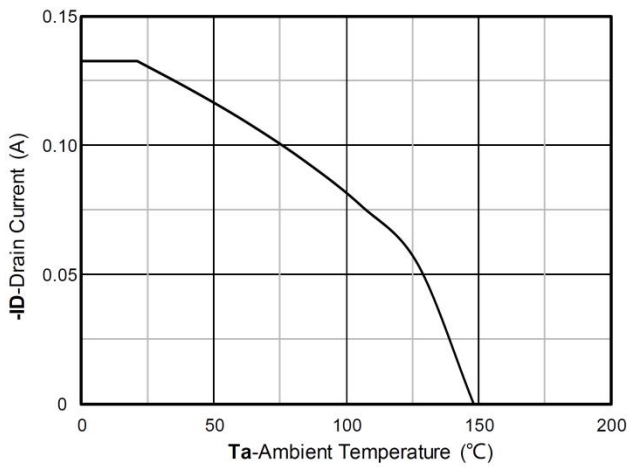
Transfer Characteristics



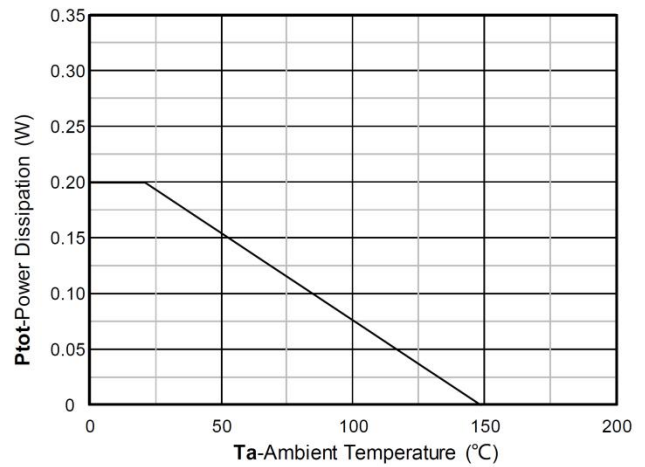
Capacitance Characteristics



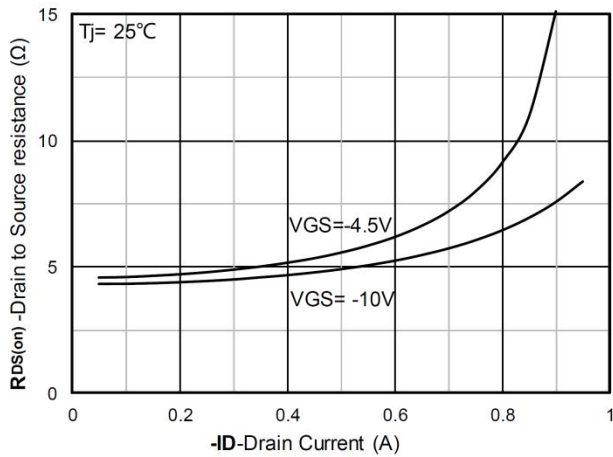
Gate Charge



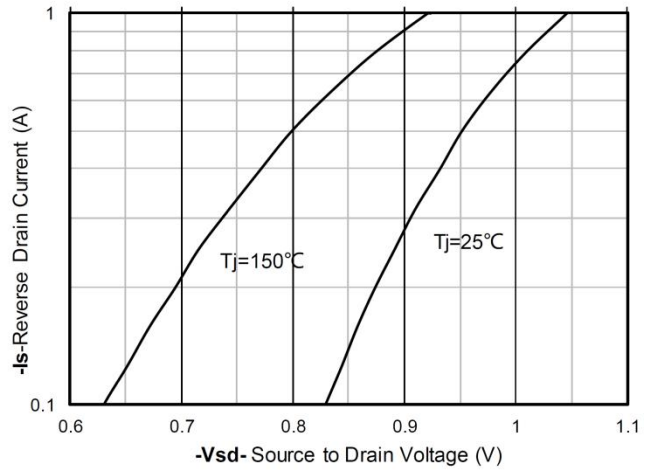
Current dissipation



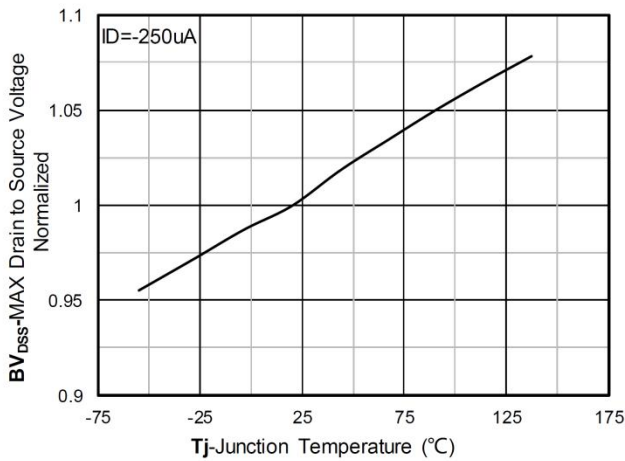
Power dissipation



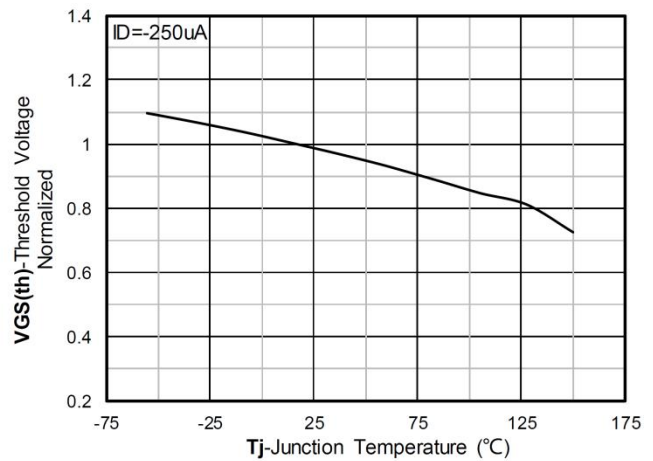
RDS(on) VS Drain Current



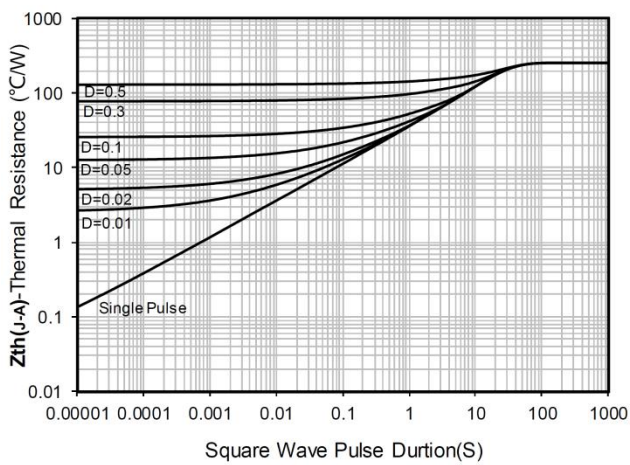
Forward characteristics of reverse diode



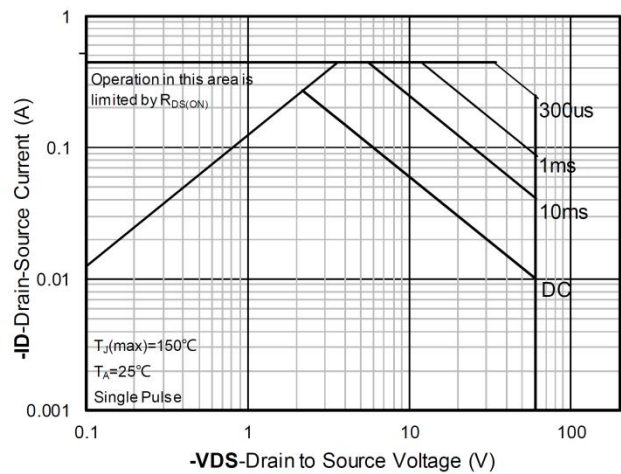
Normalized breakdown voltage



Normalized Threshold voltage

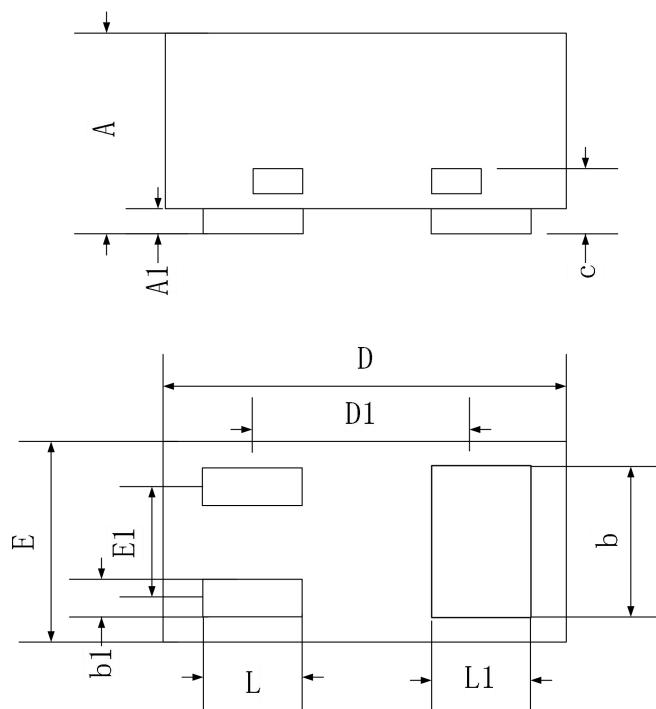


Maximum Transient Thermal Impedance



Safe Operation Area

DFN1006-3L Package Information



Symbol	Dimensions in millimeters	
	Min.	Max.
A	0.46	0.51
A1	0	0.05
b	0.45	0.55
b1	0.1	0.2
c	0.08	0.18
D	0.95	1.05
D1	0.65	
E	0.55	0.65
E1	0.325	
L	0.2	0.3
L1	0.2	0.3